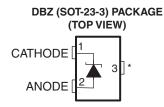


PRECISION MICROPOWER SHUNT VOLTAGE REFERENCE

Check for Samples: TL4050-Q1

FEATURES

- Qualified for Automotive Applications
- Fixed Output Voltages of 2.048 V, 2.5 V, 4.096 V, 5 V
- Tight Output Tolerances and Low Temperature Coefficient
 - Max 0.1%, 50 ppm/°C A Grade
 - Max 0.2%, 50 ppm/°C B Grade
 - Max 0.5%, 50 ppm/°C C Grade
- Low Output Noise: 41 μV_{RMS} Typ
- Wide Operating Current Range:
 60 µA Typ to 15 mA
- Stable With All Capacitive Loads; No Output



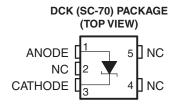
*Pin 3 is attached to Substrate and must be connected to ANODE or left open.

Capacitor Required

 Available in Extended Temperature Range: -40°C to 125°C

APPLICATIONS

- Data-Acquisition Systems
- Power Supplies and Power-Supply Monitors
- Instrumentation and Test Equipment
- Process Controls
- Precision Audio
- Automotive Electronics
- Energy Management
- Battery-Powered Equipment



NC - No internal connection

DESCRIPTION

The TL4050-Q1 family of shunt voltage references are versatile easy-to-use references suitable for a wide array of applications. The two-terminal fixed-output device requires no external capacitors for operation and is stable with all capacitive loads. Additionally, the reference offers low dynamic impedance, low noise, and low temperature coefficient to ensure a stable output voltage over a wide range of operating currents and temperatures.

The TL4050-Q1 is available in three initial tolerances, ranging from 0.1% (maximum) for the A grade to 0.5% (maximum) for the C grade. Thus, a great deal of flexibility is available to designers in choosing the best cost-to-performance ratio for their applications. Packaged in the space-saving SOT-23-3 and SC-70 packages and requiring a minimum current of 45 μ A (typical), the TL4050-Q1 also is ideal for portable applications.

The TL4050x-Q1 characterization is for operation over an ambient temperature range of -40°C to 125°C.

PACKAGE AND ORDERING INFORMATION

For the most-current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

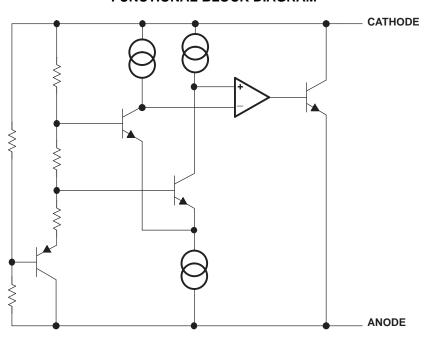
Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



FUNCTIONAL BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS(1)

over free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
IZ	Continuous cathode current	-10	20	mA
T_{J}	Operating virtual junction temperature		150	ů
T _{stg}	Storage temperature range	- 65	150	°C

⁽¹⁾ Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.



THERMAL INFORMATION

		TL405	0-Q1	
	THERMAL METRIC ⁽¹⁾	DBZ	DCK	UNIT
		3 PINS	5 PINS	
θ_{JA}	Junction-to-ambient thermal resistance (2)	331.1	289.9	°C/W
θ_{JCtop}	Junction-to-case (top) thermal resistance ⁽³⁾	107.5	56.4	°C/W
θ_{JB}	Junction-to-board thermal resistance ⁽⁴⁾	63.4	93	°C/W
Ψлт	Junction-to-top characterization parameter ⁽⁵⁾	4.9	0.7	°C/W
ΨЈВ	Junction-to-board characterization parameter ⁽⁶⁾	61.7	91.4	°C/W
θ_{JCbot}	Junction-to-case (bottom) thermal resistance (7)	N/A	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.
- (2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
- (3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
- (4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
- (5) The junction-to-top characterization parameter, ψ_{JT}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA}, using a procedure described in JESD51-2a (sections 6 and 7).
- (6) The junction-to-board characterization parameter, ψ_{JB}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA}, using a procedure described in JESD51-2a (sections 6 and 7).
- (7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

RECOMMENDED OPERATING CONDITIONS

			MIN	MAX	UNIT
IZ	Cathode current		(1)	15	mA
_	Free dir temperature	I temperature	-40	85	°C
1 A	Free-air temperature	Q temperature	-40	125	

(1) See parametric tables



TL4050x20-Q1 ELECTRICAL CHARACTERISTICS

at extended temperature range, full range $T_A = -40^{\circ}\text{C}$ to 125°C (unless otherwise noted)

Б.	DAMETED	TECT CONDITIONS	_	TL40)50A20-0	21	TL40)50B20-0	21	TL40	50C20-0	21	UNIT	
PA	RAMETER	TEST CONDITIONS	TA	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNII	
V _Z	Reverse breakdown voltage	Ι _Z = 100 μΑ	25°C		2.048			2.048			2.048		V	
	Reverse		25°C	-2.048		2.048	-4.096		4.096	-10.24		10.24		
ΔV_Z	breakdown voltage tolerance	I _Z = 100 μA	Full range	-12.288		12.288	-14.7456		14.7456	-17.2032		17.2032	mV	
	Minimum		25°C		41	60		41	60		41	60		
$I_{Z,min}$	cathode current		Full range			65			65			65	μA	
	Average	I _Z = 10 mA	25°C		±20			±20			±20			
	temperature coefficient of	I _Z = 1 mA	25°C		±15			±15			±15		nnm/00	
$\alpha_{VZ} \\$	reverse breakdown voltage		25°C		±15			±15			±15		ppm/°C	
		I _Z = 100 μA	Full range			±50			±50			±50		
	Reverse		25°C		0.3	8.0		0.3	0.8		0.3	0.8		
ΔV_Z	breakdown voltage change with	$I_{Z,min} < I_Z < 1 \text{ mA}$	Full range			1.2			1.2			1.2	mV	
ΔI_Z	cathode		25°C		2.3	6		2.3	6		2.3	6	IIIV	
	current change	1 mA < I _Z < 15 mA	Full range			8			8			8		
Z _Z	Reverse dynamic impedance	$I_Z = 1 \text{ mA},$ f = 120 Hz, $I_{AC} = 0.1 I_Z$	25°C		0.3			0.3			0.3		Ω	
e _N	Wideband noise	$I_Z = 100 \mu A,$ 10 Hz \le f \le 10 kHz	25°C		34			34			34		μV _{RMS}	
	Long-term stability of reverse breakdown voltage	t = 1000 h, T _A = 25°C ± 0.1°C, I _Z = 100 μA			120			120			120		ppm	
V _{HYST}	Thermal hysteresis (1)	$\Delta T_A = -40$ °C to 125°C			0.7			0.7			0.7		mV	

⁽¹⁾ Thermal hysteresis is defined as $V_{Z,25^{\circ}C}$ (after cycling to $-40^{\circ}C$) – $V_{Z,25^{\circ}C}$ (after cycling to $125^{\circ}C$).



TL4050x25-Q1 ELECTRICAL CHARACTERISTICS

at extended temperature range, full range $T_A = -40$ °C to 125°C (unless otherwise noted)

			_	TL4	050B25-Q1		UNIT
	PARAMETER	TEST CONDITIONS	T _A	MIN	TYP	MAX	UNII
Vz	Reverse breakdown voltage	I _Z = 100 μA	25°C		2.5		V
A) /	Reverse breakdown voltage	1 100 1	25°C	-5		5	
ΔV_Z	tolerance	$I_Z = 100 \ \mu A$	Full range	-18		18	mV
	Minimum and and a summer		25°C		41	60	
$I_{Z,min}$	Minimum cathode current		Full range			65	μΑ
		I _Z = 10 mA	25°C		±20		
~	Average temperature	I _Z = 1 mA	25°C		±15		nnm/00
α_{VZ}	coefficient of reverse breakdown voltage	100.00	25°C		±15		ppm/°C
	· ·	$I_Z = 100 \mu A$	Full range			±50	
·		1 .1 .1	25°C		0.3	0.8	
$\frac{\Delta V_Z}{\Delta I_Z}$	Reverse breakdown voltage change with cathode	$I_{Z,min} < I_Z < 1 \text{ mA}$	Full range			1.2	mV
ΔI_Z	current change	1 mA < I ₇ < 15 mA	25°C		2.3	6	IIIV
		TIMA < IZ < 15 IIIA	Full range			8	
Z_Z	Reverse dynamic impedance	$I_Z = 1 \text{ mA},$ f = 120 Hz, $I_{AC} = 0.1 I_Z$	25°C		0.3		Ω
e _N	Wideband noise	$I_Z = 100 \mu A$, 10 Hz $\leq f \leq 10 \text{ kHz}$	25°C		41		μV_{RMS}
	Long-term stability of reverse breakdown voltage	t = 1000 h, $T_A = 25^{\circ}\text{C} \pm 0.1^{\circ}\text{C},$ $I_Z = 100 \mu\text{A}$			120		ppm
V _{HYST}	Thermal hysteresis ⁽¹⁾	$\Delta T_A = -40$ °C to 125°C			0.7		mV

⁽¹⁾ Thermal hysteresis is defined as $V_{Z,25^{\circ}C}$ (after cycling to $-40^{\circ}C$) – $V_{Z,25^{\circ}C}$ (after cycling to $125^{\circ}C$).



TL4050x41-Q1 ELECTRICAL CHARACTERISTICS

at extended temperature range, full range $T_A = -40$ °C to 125°C (unless otherwise noted)

	DARAMETER	TEST COMPLETIONS	_	TL4	050B41-Q1		UNIT	
	PARAMETER	TEST CONDITIONS	T _A	MIN	TYP	MAX	UNII	
V _Z	Reverse breakdown voltage	I _Z = 100 μA	25°C		4.096		V	
A)/	Reverse breakdown voltage	1. 4004	25°C	-8.2		8.2	\/	
ΔV_Z	tolerance	$I_Z = 100 \mu A$	Full range	-29		29	mV	
	M		25°C		52	68		
I _{Z,min}	Minimum cathode current		Full range			78	μΑ	
		I _Z = 10 mA	25°C		±30			
~	Average temperature coefficient of reverse	I _Z = 1 mA	25°C		±20		nnm/0C	
α_{VZ}	breakdown voltage	100	25°C		±20		ppm/°C	
	· ·	$I_Z = 100 \ \mu A$	Full range			±50		
		1 - 1 - 1 - 1	25°C		0.2	0.9		
$\frac{\Delta V_Z}{\Delta I_Z}$	Reverse breakdown voltage		Reverse breakdown voltage change with cathode	Full range			1.2	mV
ΔI_Z	change with cathode current change	1 1 15 1	25°C		2	7	mv	
		1 mA < I _Z < 15 mA	Full range			10		
Z _Z	Reverse dynamic impedance	$I_Z = 1 \text{ mA},$ f = 120 Hz, $I_{AC} = 0.1 I_Z$	25°C		0.5		Ω	
e _N	Wideband noise	I _Z = 100 μA, 10 Hz ≤ f ≤ 10 kHz	25°C		93		μV_{RMS}	
	Long-term stability of reverse breakdown voltage	t = 1000 h, $T_A = 25^{\circ}\text{C} \pm 0.1^{\circ}\text{C},$ $I_Z = 100 \mu\text{A}$			120		ppm	
V _{HYST}	Thermal hysteresis ⁽¹⁾	$\Delta T_A = -40$ °C to 125°C			1.148		mV	

⁽¹⁾ Thermal hysteresis is defined as $V_{Z,25^{\circ}C}$ (after cycling to $-40^{\circ}C$) – $V_{Z,25^{\circ}C}$ (after cycling to $125^{\circ}C$).



TL4050x50-Q1 ELECTRICAL CHARACTERISTICS

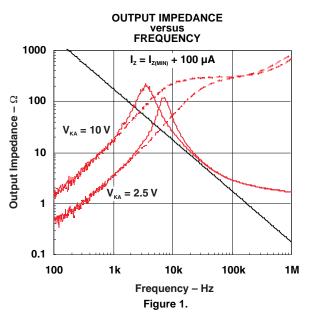
at extended temperature range, full range $T_A = -40$ °C to 125°C (unless otherwise noted)

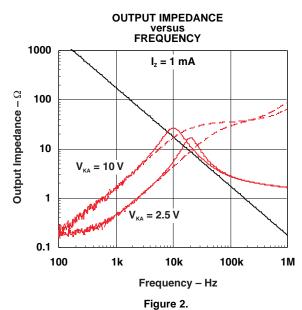
		TEST SOMBITIONS	_	TL40	50A50-Q	1	TL4	050B50-C	11	TL40	050C50-C	21	LINUT	
,	PARAMETER	TEST CONDITIONS	T _A	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
V _Z	Reverse breakdown voltage	Ι _Z = 100 μΑ	25°C		5			5			5		V	
	Reverse		25°C	- 5		5	-10		10	-25		25		
ΔV_Z	breakdown voltage tolerance	I _Z = 100 μA	Full range	-30		30	-35		35	-50		50	mV	
	Minimum		25°C		56	74		56	74		56	74		
I _{Z,min}	cathode current		Full range			90			90			90	μA	
	Average	I _Z = 10 mA	25°C		±30			±30			±30			
	temperature	I _Z = 1 mA	25°C		±20			±20			±20			
α_{VZ}	coefficient of reverse		25°C		±20			±20			±20		ppm/°C	
	breakdown voltage		I _Z = 100 μA	Full range			±50			±50			±50	
			25°C		0.2	1		0.2	1		0.2	1		
ΔV_Z	Reverse breakdown voltage change	$I_{Z,min} < I_Z < 1 \text{ mA}$	Full range			1.4			1.4			1.4	mV	
ΔI_Z	with cathode		25°C		2	8		2	8		2	8	IIIV	
	current change	1 mA < I _Z < 15 mA	Full range			12			12			12		
Z _Z	Reverse dynamic impedance	$I_Z = 1 \text{ mA},$ f = 120 Hz, $I_{AC} = 0.1 I_Z$	25°C		0.5			0.5			0.5		Ω	
e _N	Wideband noise	$I_Z = 100 \mu A$, 10 Hz \le f \le 10 kHz	25°C		93			93			93		μV_{RMS}	
	Long-term stability of reverse breakdown voltage	t = 1000 h, T _A = 25°C ± 0.1°C, I _Z = 100 μA			120			120			120		ppm	
V _{HYST}	Thermal hysteresis (1)	$\Delta T_A = -40$ °C to 125°C			1.4			1.4			1.4		mV	

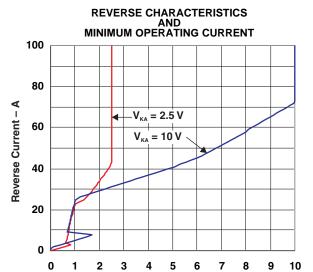
⁽¹⁾ Thermal hysteresis is defined as $V_{Z,25^{\circ}C}$ (after cycling to $-40^{\circ}C$) – $V_{Z,25^{\circ}C}$ (after cycling to $125^{\circ}C$).



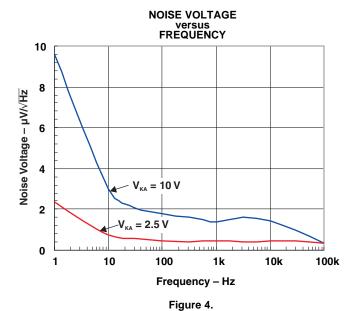
TYPICAL CHARACTERISTICS



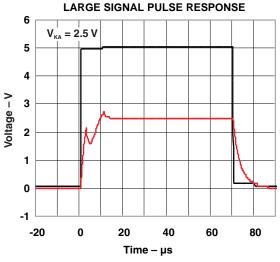




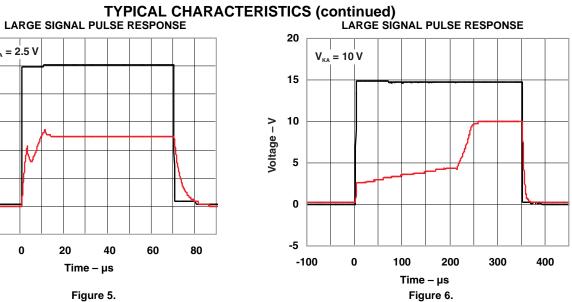
Reverse Voltage (V) Figure 3.













APPLICATION INFORMATION

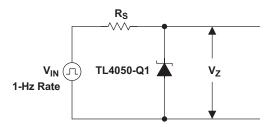


Figure 7. Start-Up Test Circuit

Output Capacitor

The TL4050-Q1 does not require an output capacitor across cathode and anode for stability. However, in an application using an output bypass capacitor, the TL4050-Q1 is stable with all capacitive loads.

SOT-23-3 Pin Connections

There is a parasitic Schottky diode connected between pins 2 and 3 of the SOT-23-3 packaged device. Thus, pin 3 of the SOT-23-3 package must be left floating or connected to pin 2.

Use With ADCs or DACs

The design of the TL4050x41-Q1 is as a cost-effective voltage reference, as required in 12-bit data-acquisition systems. For 12-bit systems operating from 5-V supplies, such as the ADS7842 (see Figure 8), the TL4050x41-Q1 (4.096 V) permits operation with an LSB of 1 mV.

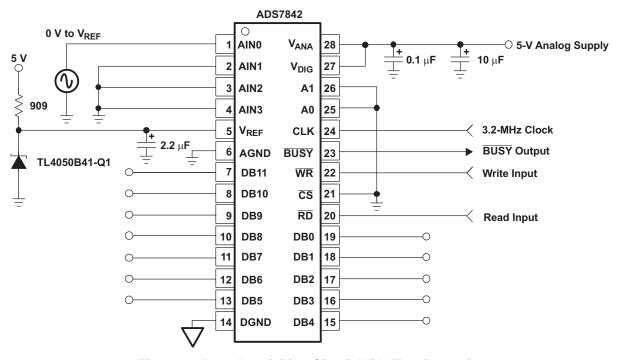


Figure 8. Data-Acquisition Circuit With TL4050x41-Q1



Cathode and Load Currents

In a typical shunt-regulator configuration (see Figure 9), an external resistor, R_S , connects between the supply and the cathode of the TL4050-Q1. Proper choice of R_S is essential, as R_S sets the total current available to supply the load (I_L) and bias the TL4050-Q1 (I_Z). In all cases, I_Z must stay within a specified range for proper operation of the reference. Taking into consideration one extreme in the variation of the load and supply voltage (maximum I_L and minimum V_S), R_S must be small enough to supply the minimum I_Z required for operation of the regulator, as given by data-sheet parameters. At the other extreme, maximum V_S and minimum I_L , R_S must be large enough to limit I_Z to less than its maximum-rated value of 15 mA.

Equation 1 calculates R_S:

$$R_{S} = \frac{(V_{S} - V_{Z})}{(I_{L} + I_{Z})} \tag{1}$$

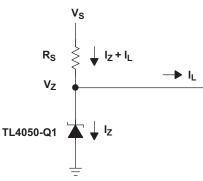


Figure 9. Shunt Regulator





10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
	, ,					.,	(6)	, ,		• •	
TL4050A50QDBZRQ1	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TLGU	Samples
TL4050A50QDCKRQ1	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	7GU	Samples
TL4050B25QDBZRQ1	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TLHU	Samples
TL4050B25QDCKRQ1	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	7HU	Samples
TL4050B41QDBZRQ1	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TMXU	Samples
TL4050B50QDBZRQ1	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TLJU	Samples
TL4050B50QDCKRQ1	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	7JU	Samples
TL4050C20QDBZRQ1	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TMYU	Samples
TL4050C50QDBZRQ1	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TKZU	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.



PACKAGE OPTION ADDENDUM

10-Dec-2020

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 5-Jan-2021

TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TL4050A50QDBZRQ1	SOT-23	DBZ	3	3000	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TL4050A50QDCKRQ1	SC70	DCK	5	3000	179.0	8.4	2.2	2.5	1.2	4.0	8.0	Q3
TL4050B25QDBZRQ1	SOT-23	DBZ	3	3000	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TL4050B25QDCKRQ1	SC70	DCK	5	3000	179.0	8.4	2.2	2.5	1.2	4.0	8.0	Q3
TL4050B41QDBZRQ1	SOT-23	DBZ	3	3000	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TL4050B50QDBZRQ1	SOT-23	DBZ	3	3000	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TL4050B50QDCKRQ1	SC70	DCK	5	3000	179.0	8.4	2.2	2.5	1.2	4.0	8.0	Q3
TL4050C20QDBZRQ1	SOT-23	DBZ	3	3000	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3
TL4050C50QDBZRQ1	SOT-23	DBZ	3	3000	179.0	8.4	3.15	2.95	1.22	4.0	8.0	Q3

www.ti.com 5-Jan-2021



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TL4050A50QDBZRQ1	SOT-23	DBZ	3	3000	200.0	183.0	25.0
TL4050A50QDCKRQ1	SC70	DCK	5	3000	200.0	183.0	25.0
TL4050B25QDBZRQ1	SOT-23	DBZ	3	3000	200.0	183.0	25.0
TL4050B25QDCKRQ1	SC70	DCK	5	3000	200.0	183.0	25.0
TL4050B41QDBZRQ1	SOT-23	DBZ	3	3000	200.0	183.0	25.0
TL4050B50QDBZRQ1	SOT-23	DBZ	3	3000	200.0	183.0	25.0
TL4050B50QDCKRQ1	SC70	DCK	5	3000	200.0	183.0	25.0
TL4050C20QDBZRQ1	SOT-23	DBZ	3	3000	200.0	183.0	25.0
TL4050C50QDBZRQ1	SOT-23	DBZ	3	3000	200.0	183.0	25.0

DCK (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AA.



DCK (R-PDSO-G5)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.





Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4203227/C





SMALL OUTLINE TRANSISTOR



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 Reference JEDEC registration TO-236, except minimum foot length.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 4. Publication IPC-7351 may have alternate designs.5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 7. Board assembly site may have different recommendations for stencil design.



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